

## **KSA1175**

### **Low Frequency Amplifier**

- Collector-Base Voltage : V<sub>CBO</sub>= -60V
  Complement to KSC2785



1.Emitter 2. Collector 3. Base

## **PNP Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V <sub>CBO</sub>	Collector-Base Voltage	-60	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V	
I <sub>C</sub>	Collector Current	-150	mA	
P <sub>C</sub>	Collector Power Dissipation	250	mW	
T <sub>J</sub>	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C	

## $\textbf{Electrical Characteristics} \ \, \textbf{T}_{\textbf{a}} = 25 ^{\circ} \textbf{C} \ \, \textbf{unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C}=-100\mu A, I_{E}=0$	-60			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-50			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E}$ = -10 $\mu$ A, $I_{C}$ =0	-5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -60V, I <sub>E</sub> =0			-0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-0.1	μΑ
h <sub>FE</sub>	DC Current Gain	$V_{CE}$ = -6V, $I_{C}$ = -1mA	40		700	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA		-0.18	-0.3	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ = -6V, $I_{E}$ = -1mA	-0.50	-0.62	-0.80	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE}$ = -6V, $I_{C}$ = -10mA	50	180		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHz		2.8		pF
NF	Noise Figure	$V_{CE}$ = -6V, $I_{C}$ = -0.3mA f=100Hz, $R_{S}$ =10K $\Omega$		6.0	20	dB

## **h**<sub>FE</sub> Classification

Classification	R	0	Y	G	L
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240	200 ~ 400	350 ~ 700

## **Typical Characteristics**

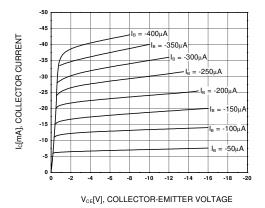


Figure 1. Static Characteristic

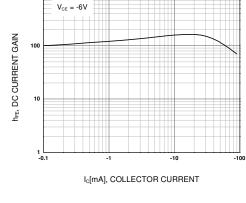


Figure 2. DC current Gain

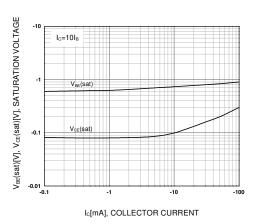


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

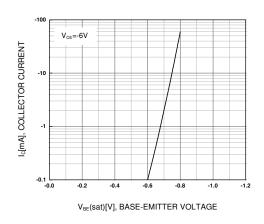


Figure 4. Base-Emitter On Voltage

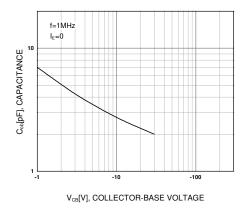


Figure 5. Collector Output Capacitance

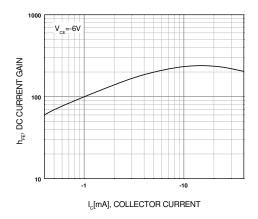
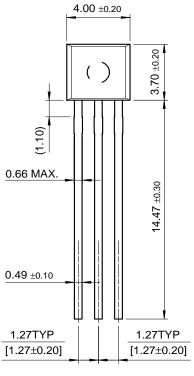


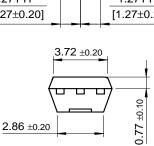
Figure 6. Current Gain Bandwidth Product

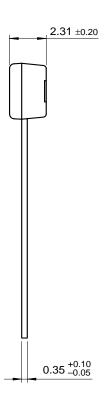
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# **Package Dimensions**

**TO-92S** 







Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	OCXTM	RapidConfigure™	UHC™
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The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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Rev. I1

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